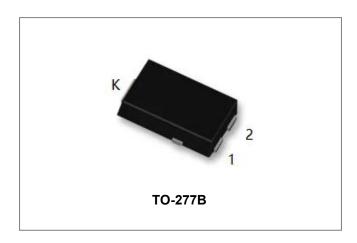




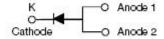
### ST5100S SCHOTTKY RECTIFIER



#### **Features**

- 150°C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- "-A" is an AEC-Q101 qualified device
- Trench MOS Schottky technology
- This is a Halogen Free Device
- All SMC parts are traceable to the wafer lot
- · Additional testing can be offered upon request

### **Circuit Diagram**



### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	100	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @T∟=125°C, rectangular wave form	5	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>c</sub> = 25 °C	120	Α

### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 2.5A, Pulse, T <sub>J</sub> = 25 °C	0.55	-	V
	VF1	@ 5A, Pulse, T <sub>J</sub> = 25 °C	0.69	0.75	V
	$V_{F2}$	@ 2.5A, Pulse, T <sub>J</sub> = 125 °C	0.49	-	V
	VF2	@ 5A, Pulse, T <sub>J</sub> = 125 °C	0.61	0.70	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_{R_1} T_J = 25 ^{\circ}\text{C}$	0.006	0.12	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	2	18	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	400	-	pF

<sup>\*</sup> Pulse width < 300  $\mu$ s, duty cycle < 2%

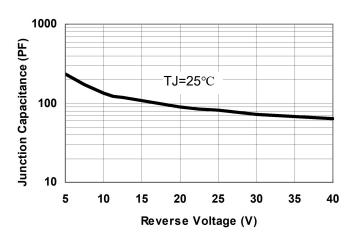




# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>θ</sub> JC	-	3.5	°C/W
Typical Thermal Resistance Junction to Ambient	R <sub>θJA</sub>		70	°C/W
Approximate Weight	wt	-	0.08	g

# **Ratings and Characteristics Curves**



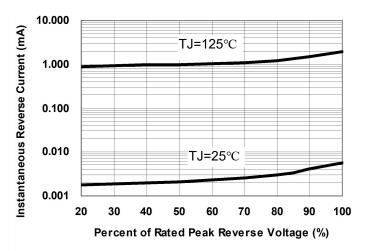


Fig.1-Typical Junction Capacitance

**Fig.2-Typical Reverse Current** 

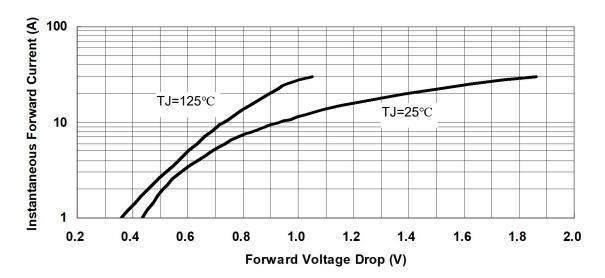


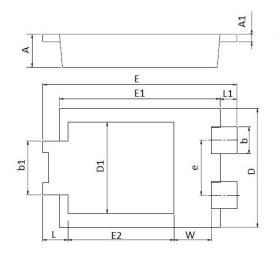
Fig.3-Typical Forward Voltage Drop Characteristics

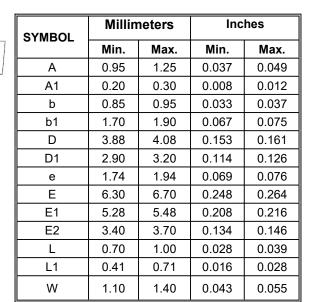
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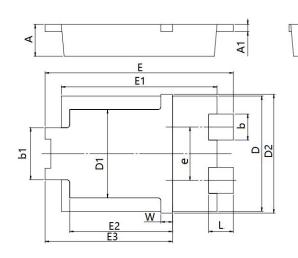


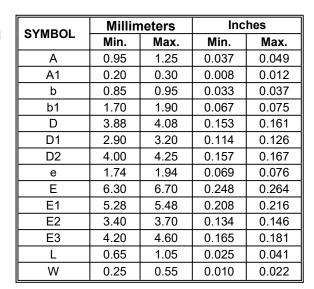
### **Mechanical Dimensions TO-277B**





### **Mechanical Dimensions TO-277B(New)**





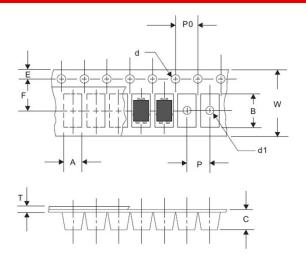
Notes: New Mechanical Dimensions is performed from date code 2236X.

http://www.smc-diodes.com - sales@ smc-diodes.com •





## **Carrier Tape Specification TO-277B**



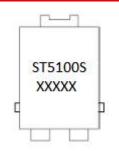
SYMBOL	Millimeters		
	Min.	Max.	
Α	4.28	4.48	
В	6.80	7.10	
С	1.30	1.50	
d	1.40	1.60	
d1	-	1.50	
E	1.65	1.85	
F	5.40	5.60	
Р	7.90	8.10	
P0	3.90	4.10	
Т	0.24	0.44	
W	11.70	12.30	

# **Ordering Information**

Device	Package	Shipping
ST5100S	TO-277B(Pb-Free)	5000pcs/ reel
ST5100STR	TO-277B(Pb-Free)	5000pcs/ reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

### **Marking Diagram**



#### Where XXXXX is YYWWL

 ST
 = Device Type

 5
 = Forward Current (5A)

 100
 = Reverse Voltage (100V)

 S
 = Package type

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0





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